

74V1T77

SINGLE D-TYPE LATCH

SOT323-5L

74V1T77CTR

- HIGH SPEED: $t_{PD} = 4.7 \text{ns}$ (TYP.) at $V_{CC} = 5 \text{V}$
- LOW POWER DISSIPATION: $I_{CC} = 1\mu A(MAX.)$ at $T_A = 25^{\circ}C$
- COMPATIBLE WITH TTL OUTPUTS: $V_{IH} = 2V (MIN), V_{IL} = 0.8V (MAX)$
- POWER DOWN PROTECTION ON INPUTS
- SYMMETRICAL OUTPUT IMPEDANCE: $|I_{OH}| = I_{OL} = 8mA (MIN)$ at $V_{CC} = 4.5V$
- BALANCED PROPAGATION DELAYS: t_{PLH} ≅ t_{PHL}
- OPERATING VOLTAGE RANGE: $V_{CC}(OPR) = 4.5V \text{ to } 5.5V$
- IMPROVED LATCH-UP IMMUNITY



DESCRIPTION

The 74V1T77 is an advanced high-speed CMOS SINGLE D-TYPE LATCH fabricated with sub-micron silicon gate and double-layer metal wiring C²MOS technology. It is designed to operate from 4.5V to 5.5V, making this device ideal for portable applications.

The single D-Type latch is controlled by an Latch Enable Input (LE). While the LE input is held at a high level, the Q output will follow the data input precisely. When the LE input is taken low the Q output is latched precisely at the logic level of D data input.

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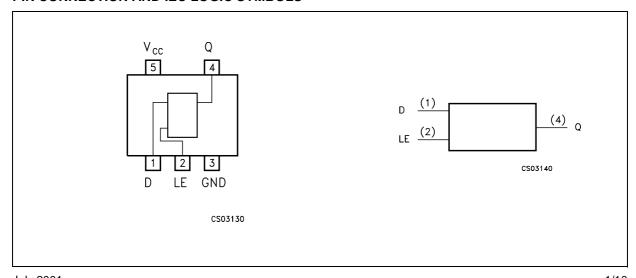
SOT323-5L

Power down protection is provided on inputs and 0 to 7V can be accepted on inputs with no regard to the supply voltage. This device can be used to interface 5V to 3V.

It's available in the commercial and extended temperature range.

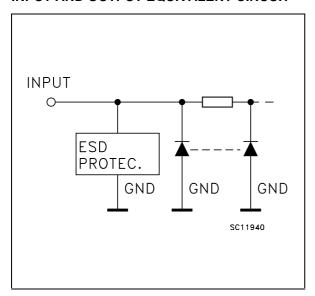
All inputs and output are equipped with protection circuits against static discharge, giving them ESD immunity and transient excess voltage.

PIN CONNECTION AND IEC LOGIC SYMBOLS



July 2001 1/10

INPUT AND OUTPUT EQUIVALENT CIRCUIT



PIN DESCRIPTION

PIN No	SYMBOL	NAME AND FUNCTION			
1	D	Data Input			
2	LE	Latch Enable Input			
4	Q	Data Output			
3	GND	Ground (0V)			
5	V _{CC}	Positive Supply Voltage			

TRUTH TABLE

D	LE	Q
L	L	No Change *
Н	L	No Change *
L	Н	L
Н	Н	Н

 $^{(\}mbox{^{*}})$ Q output is latched at the time when the LE input is taken low logic level.

ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{CC}	Supply Voltage	-0.5 to +7.0	V
VI	DC Input Voltage	-0.5 to +7.0	V
V _O	DC Output Voltage	-0.5 to V _{CC} + 0.5	V
I _{IK}	DC Input Diode Current	- 20	mA
I _{OK}	DC Output Diode Current	± 20	mA
Io	DC Output Current	± 25	mA
I _{CC} or I _{GND}	DC V _{CC} or Ground Current	± 50	mA
T _{stg}	Storage Temperature	-65 to +150	°C
T _L	Lead Temperature (10 sec)	300	°C

Absolute Maximum Ratings are those values beyond which damage to the device may occur. Functional operation under these conditions is not implied

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Value	Unit
V _{CC}	Supply Voltage	4.5 to 5.5	V
V _I	Input Voltage	0 to 5.5	V
V _O	Output Voltage	0 to V _{CC}	V
T _{op}	Operating Temperature	-55 to 125	°C
dt/dv	Input Rise and Fall Time (note 1) ($V_{CC} = 5.0 \pm 0.5V$)	0 to 20	ns/V

1) V_{IN} from 0.8V to 2V

DC SPECIFICATIONS

		1	est Condition	Value							
Symbol	Parameter	v _{cc}		Т	T _A = 25°C			85°C	-55 to 125°C		Unit
		(V)		Min.	Тур.	Max.	Min.	Max.	Min.	Max.	
V _{IH}	High Level Input Voltage	4.5 to 5.5		2			2		2		V
V _{IL}	Low Level Input Voltage	4.5 to 5.5				0.8		0.8		0.8	V
V _{OH}	High Level Output	4.5	I _O =-50 μA	4.4	4.5		4.4		4.4		V
	Voltage	4.5	I _O =-8 mA	3.94			3.8		3.7		
V _{OL}	Low Level Output	4.5	I _O =50 μA		0.0	0.1		0.1		0.1	V
	Voltage	4.5	I _O =8 mA			0.36		0.44		0.55	
I _I	Input Leakage Current	0 to 5.5	V _I = 5.5V or GND			± 0.1		± 1.0		± 1.0	μΑ
I _{CC}	Quiescent Supply Current	5.5	V _I = V _{CC} or GND			1		10		20	μΑ
△Icc	Additional Worst Case Supply Current	5.5	One Input at 3.4V, other input at V _{CC} or GND			1.35		1.5		1.5	mA

AC ELECTRICAL CHARACTERISTICS (Input $t_r = t_f = 3ns$)

		Test Condition			Value							
Symbol	Parameter	V _{CC}	V) (pF)	Cı	T _A = 25°C			-40 to 85°C		-55 to 125°C		Unit
		(V)		Min.	Тур.	Max.	Min.	Max.	Min.	Max.		
t _{PLH} t _{PHL}	Propagation Delay	5.0 (*)	15			4.4	6.5	1.0	7.5	1.0	8.5	ns
Time LE to Q	5.0 (*)	50			4.8	7.0	1.0	8.0	1.0	9.0	115	
t _{PLH} t _{PHL}	Propagation Delay	5.0 (*)	15			4.7	6.5	1.0	7.5	1.0	8.5	ns
	Time D to Q	5.0 (*)	50			5.3	7.0	1.0	8.0	1.0	9.0	115
t _W	LE Pulse Width, HIGH	5.0 (*)			3.0			3.0		3.0		ns
t _s	Setup Time D to LE, HIGH or LOW	5.0 (*)			2.0			2.0		2.0	·	ns
t _h	Hold Time D to LE, HIGH or LOW	5.0 (*)			1.0			1.0		1.0		ns

^(*) Voltage range is $5.0V \pm 0.5V$

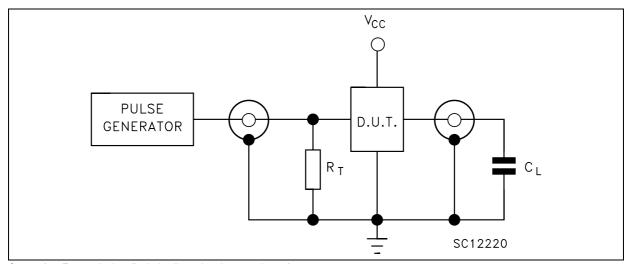
CAPACITIVE CHARACTERISTICS

		Test Condition		Value						
Symbol	Parameter		T _A = 25°C -40 to 85°C -55 to 129		125°C	Unit				
			Min.	Тур.	Max.	Min.	Max.	Min.	Max.	
C _{IN}	Input Capacitance			4	10		10		10	pF
C _{PD}	Power Dissipation Capacitance (note 1)			8						pF

¹⁾ C_{PD} is defined as the value of the IC's internal equivalent capacitance which is calculated from the operating current consumption without load. (Refer to Test Circuit). Average operating current can be obtained by the following equation. $I_{CC(opr)} = C_{PD} \times V_{CC} \times f_{IN} + I_{CC}$

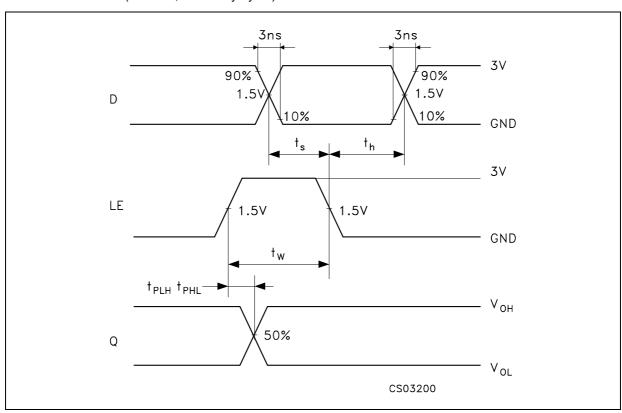


TEST CIRCUIT

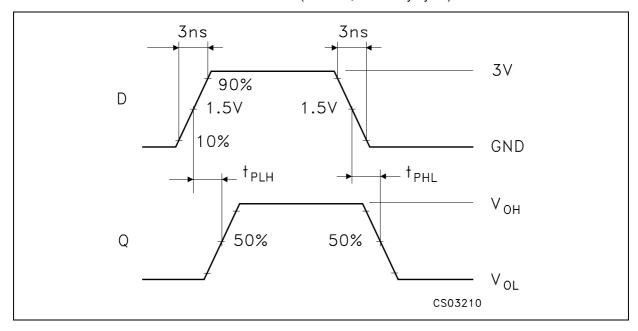


 C_L = 15/50pF or equivalent (includes jig and probe capacitance) R_T = Z_{OUT} of pulse generator (typically 50 Ω)

WAVEFORM 1: LE TO Qn PROPAGATION DELAYS, LE MINIMUN PULSE WIDTH, Dn TO LE SETUP AND HOLD TIMES (f=1MHz; 50% duty cycle)

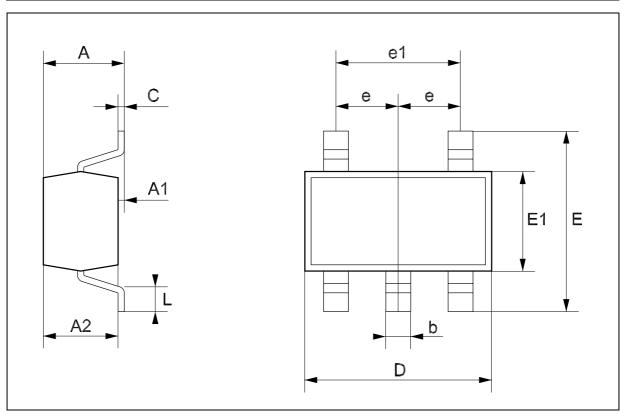


WAVEFORM 2: PROPAGATION DELAY TIME (f=1MHz; 50% duty cycle)



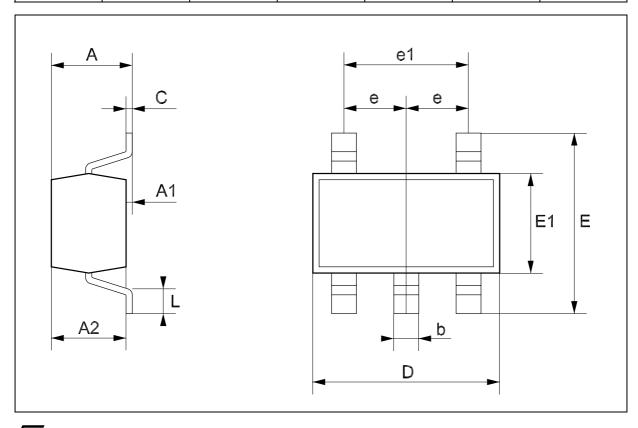
SOT23-5L MECHANICAL DATA

DIM		mm.		mils			
DIM.	MIN.	TYP	MAX.	MIN.	TYP.	MAX.	
А	0.90		1.45	35.4		57.1	
A1	0.00		0.15	0.0		5.9	
A2	0.90		1.30	35.4		51.2	
b	0.35		0.50	13.7		19.7	
С	0.09		0.20	3.5		7.8	
D	2.80		3.00	110.2		118.1	
E	2.60		3.00	102.3		118.1	
E1	1.50		1.75	59.0		68.8	
е		0.95			37.4		
e1		1.9			74.8		
L,	0.35		0.55	13.7		21.6	

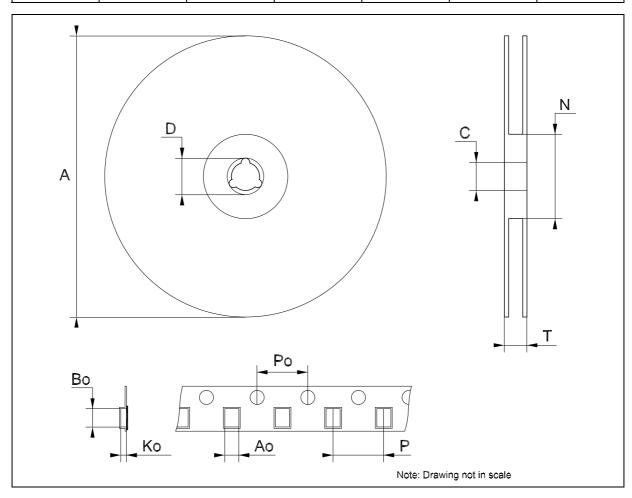


SOT323-5L MECHANICAL DATA

DIM		mm.		mils			
DIM.	MIN.	TYP	MAX.	MIN.	TYP.	MAX.	
А	0.80		1.10	31.5		43.3	
A1	0.00		0.10	0.0		3.9	
A2	0.80		1.00	31.5		39.4	
b	0.15		0.30	5.9		11.8	
С	0.10		0.18	3.9		7.1	
D	1.80		2.20	70.9		86.6	
E	1.80		2.40	70.9		94.5	
E1	1.15		1.35	45.3		53.1	
е		0.65			25.6		
e1		1.3			51.2		
L	0.10		0.30	3.9		11.8	

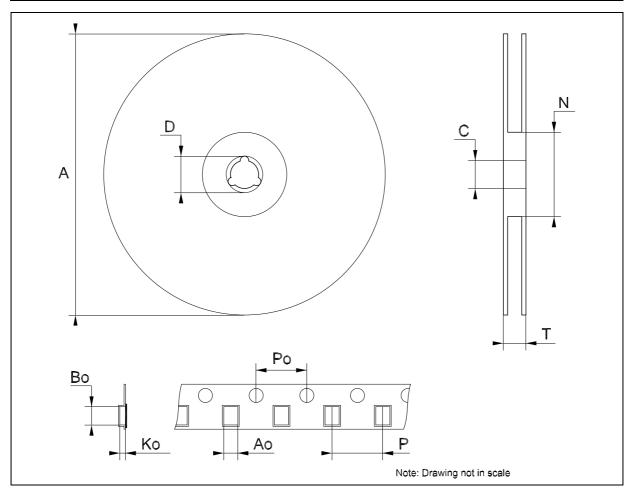


DIM		mm.		inch				
DIM.	MIN.	TYP	MAX.	MIN.	TYP.	MAX.		
Α			180			7.086		
С	12.8	13.0	13.2	0.504	0.512	0.519		
D	20.2			0.795				
N	60			2.362				
Т			14.4			0.567		
Ao	3.13	3.23	3.33	0.123	0.127	0.131		
Во	3.07	3.17	3.27	0.120	0.124	0.128		
Ko	1.27	1.37	1.47	0.050	0.054	0.0.58		
Ро	3.9	4.0	4.1	0.153	0.157	0.161		
Р	3.9	4.0	4.1	0.153	0.157	0.161		



Tape & Reel SOT323-xL MECHANICAL DATA

DIM		mm.		inch			
DIM.	MIN.	TYP	MAX.	MIN.	TYP.	MAX.	
А	175	180	185	6.889	7.086	7.283	
С	12.8	13	13.2	0.504	0.512	0.519	
D	20.2			0.795			
N	59.5	60	60.5		2.362		
Т			14.4			0.567	
Ao		2.25			0.088		
Во		2.7			0.106		
Ko		1.2			0.047		
Ро	3.98	4	4.2	0.156	0.157	0.165	
Р	3.98	4	4.2	0.156	0.157	0.165	



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